Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-1674	SERIAL NO. 09/920,978
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U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	3,990,927	11/09/76	Montier	156	8	
	AB	4,474,975	10/02/84	Clemons et al.	556	410	
	AC	5,156,881	10/20/92	Okano et al.	427	572	
	AD	5,182,221	01/26/93	Sato	437	67	
	AE	5,410,176	04/25/95	Liou et al.	257	50	
	AF	5,470,798	11/28/95	Ouellet	437	231	
	AG	5,719,085	02/17/98	Moon et al.	438	424	
	AH	5,741,740	04/21/98	Jang et al.	438	435	
	AI	5,776,557	07/07/98	Okano et al.	427	579	
	AJ	5,786,039	07/28/98	Brouquet	427	578	
	AK	5,801,083	09/01/98	Yu et al.	438	424	

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		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
	AL							
	AM							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AN		Beekmann et al., *Sub-micron Gap Fill and In-Situ Planarisation Using Flowfill™ Technology,* Electrotech, Presented at ULSI Conference, Portland, Oregon (October 1995).
	AO		Horie et al., *Kinetics and Methanism of the Reactions of $O(^3P)$ With SiH_4, CH_3SiH_3, $(CH_3)_2SiH_2$, and $(CH_3)_3SiH$,* 95 J. PHYS. CHEM. No. 95, pp. 4393-4400 (1991).
	AP		Joshi et al., *Plasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography*, 1925 SPIE 709-720 (1993).

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	AA	5,863,827	01/26/99	Joyner	438	425	
	AB	5,883,006	03/16/99	Iba	438	712	
DS	AC	5,888,880	03/30/99	Gardner et al.	438	424	
DS	AD	5,895,253	04/20/99	Akram	438	424	
DS	AE	5,904,540	05/18/99	Sheng et al.	438	427	
DS	AF	5,930,645	07/27/99	Lyons et al.	438	424	
DS	AG	5,943,585	08/24/99	May et al.	438	400	
DS	AH	5,950,094	09/07/99	Lin et al.	438	409	
DS	AI	5,960,299	09/28/99	Yew et al.	438	424	
DS	AJ	5,972,773	10/26/99	Liu et al.	438	424	
DS	AK	5,998,280	12/07/99	Bergemont et al.	438	425	

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DS	AN		Kiermasz et al., *Planarization for Sub-Micron Devices Utilising a New Chemistry*, Electrotech,
			Presented at DUMIC Conference, California (February 1995).
DS	AO		Matsuura et al., *A Highly Reliable Self-planarizing Low-k Intermetal Dielectric for Sub-quarter*
			Micron Interconnects, IEEE 785-788 (1997).
DS	AP		Matsuura et al., *Novel Self-planarizing CVD Oxide for Interlayer Dielectric Applications*, IEEE
			117-120 (1994).

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DS	1/13/03

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	AA	6,030,881	02/29/00	Papasouliotis et al.	438	424	
	AB	6,051,477	04/18/00	Nam	438	404	
	AC	6,156,674	12/05/00	Li et al.	438	780	
	AD	6,300,219 B1	10/09/01	Doan et al.	438	424	
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AN		McClatchie et al., *Low Dielectric Constant Flowfill® Technology for IMD Applications*, 7 pages (pre-August 1993).
	AO		Withnall et al., *Matrix Reactions of Methylsilanes and Oxygen Atoms*, 92 J. PHYS. CHEM., No. 3, pp. 594-602 (1988)
	AP		

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